

Dual N-Channel Enhancement Mode MOSFET

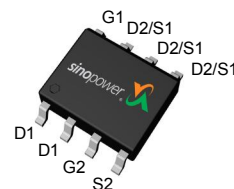
Features

- Channel 1**
 30V/6.8A,
 $R_{DS(ON)} = 21.5m\Omega$ (max.) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 30m\Omega$ (max.) @ $V_{GS} = 4.5V$
- Channel 2 (Integrated Schottky Diode)**
 30V/10.3A,
 $R_{DS(ON)} = 10.5m\Omega$ (max.) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 17m\Omega$ (max.) @ $V_{GS} = 4.5V$
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)
- 100% UIS tested

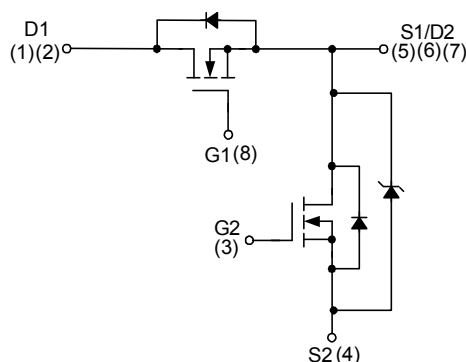
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems

Pin Description

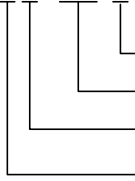


Top View of SOP – 8



N-Channel MOSFET

Ordering and Marking Information

SM4913TS □□-□□□  Assembly Material Handling Code Temperature Range Package Code	Package Code K : SOP-8 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel (2500ea/reel) Assembly Material G : Halogen and Lead Free Device
SM4913TS K : 	XXXXX - Lot Code

Note : SINOPOWER lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. SINOPOWER lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020D for MSL classification at lead-free peak reflow temperature. SINOPOWER defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

SINOPOWER reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Channel 1	Channel 2	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)					
V _{DSS}	Drain-Source Voltage		30	30	V
V _{GSS}	Gate-Source Voltage		±20	±20	
T _J	Maximum Junction Temperature		150		°C
T _{STG}	Storage Temperature Range		-55 to 150		
I _S	Diode Continuous Forward Current	T _A =25°C	1.5	2	A
I _{SM}	Pulsed Diode Forward Current	T _A =25°C	22	25	
I _D	Continuous Drain Current	T _A =25°C	6.8	10.3	
I _{DM} ^a	Pulsed Drain Current	T _A =25°C	17	25	
P _D	Power Dissipation	T _A =25°C	1.5	1.7	W
		T _A =70°C	1	1.1	
R _{θJA}	Thermal Resistance-Junction to Ambient	t ≤ 10s	50	40	°C/W
		Steady State	80	70	
R _{θJL}	Thermal Resistance-Junction to Lead	Steady State	20	16	
I _{AS} ^b	Avalanche Current, Single pulse (L=0.1mH)		10	20	A
E _{AS} ^b	Avalanche Energy, Single pulse (L=0.1mH)		5	20	mJ

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^\circ\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Channel 1

Symbol	Parameter	Test Conditions	Channel 1			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.5	1.8	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =8A	-	18	21.5	mΩ
		V _{GS} =4.5V, I _{DS} =5A	-	23	30	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.75	1.1	V
t _{rr}	Reverse Recovery Time	I _{DS} =8A, di _{SD} /dt=100A/μs	-	9	-	ns
Q _{rr}	Reverse Recovery Charge		-	3.6	-	nC
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.6	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	400	-	pF
C _{oss}	Output Capacitance		-	77	-	
C _{rss}	Reverse Transfer Capacitance		-	40	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	5.4	8	ns
t _r	Turn-on Rise Time		-	9	13	
t _{d(OFF)}	Turn-off Delay Time		-	13.2	20	
t _f	Turn-off Fall Time		-	3.2	4.8	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =8A	-	8.2	12	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =8A	-	3.9	-	
Q _{gs}	Gate-Source Charge		-	0.78	-	
Q _{gd}	Gate-Drain Charge		-	2.2	-	
Q _{gth}	Threshold Gate Charge		-	0.47	-	

Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Channel 2

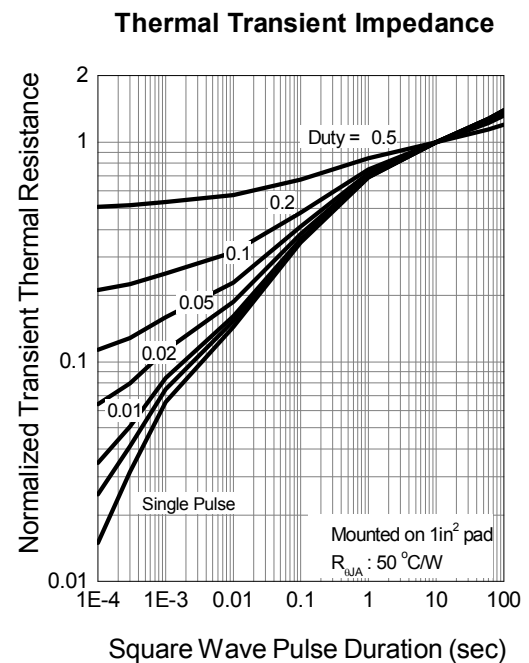
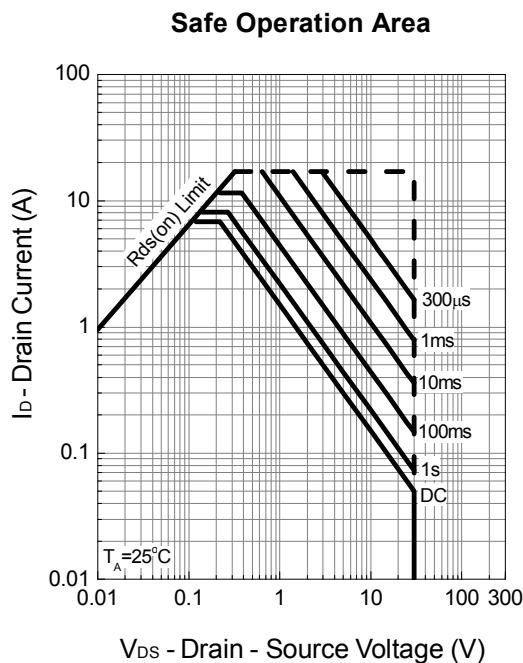
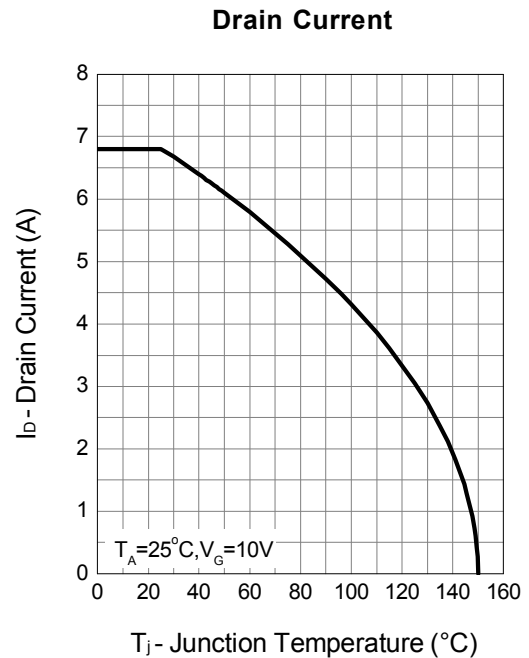
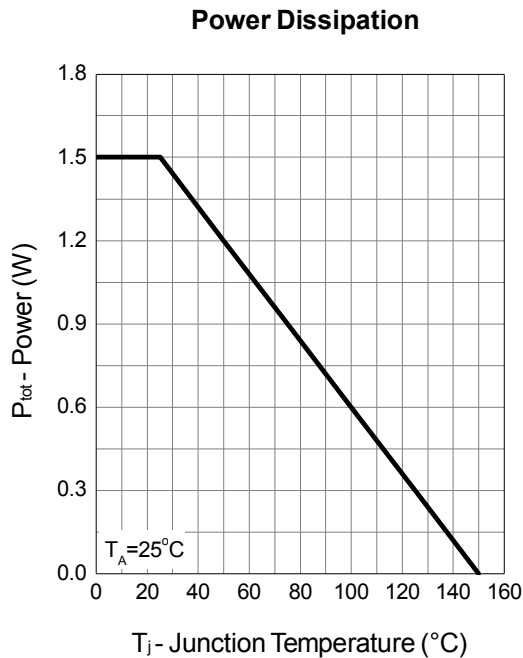
Symbol	Parameter	Test Conditions	Channel 2			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	50	μA
		T _J =85°C	-	-	5	mA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1.3	1.7	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =13A	-	8.7	10.5	mΩ
		V _{GS} =4.5V, I _{DS} =10A	-	13	17	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.4	0.55	V
		I _{SD} =10A, V _{GS} =0V	-	0.77	1.1	
t _{rr}	Reverse Recovery Time	I _{sd} =5A, dl _{SD} /dt=100A/μs	-	14	-	ns
Q _{rr}	Reverse Recovery Charge		-	5.3	-	nC
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.9	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	900	-	pF
C _{oss}	Output Capacitance		-	200	-	
C _{rss}	Reverse Transfer Capacitance		-	90	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =1Ω	-	8.6	13	ns
t _r	Turn-on Rise Time		-	10	15	
t _{d(OFF)}	Turn-off Delay Time		-	20.4	30	
t _f	Turn-off Fall Time		-	6	9	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =13A	-	17.3	25	nC
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =13A	-	8.5	-	
Q _{gs}	Gate-Source Charge		-	1.5	-	
Q _{gd}	Gate-Drain Charge		-	5.5	-	
Q _{gth}	Threshold Gate Charge		-	0.75	-	

Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

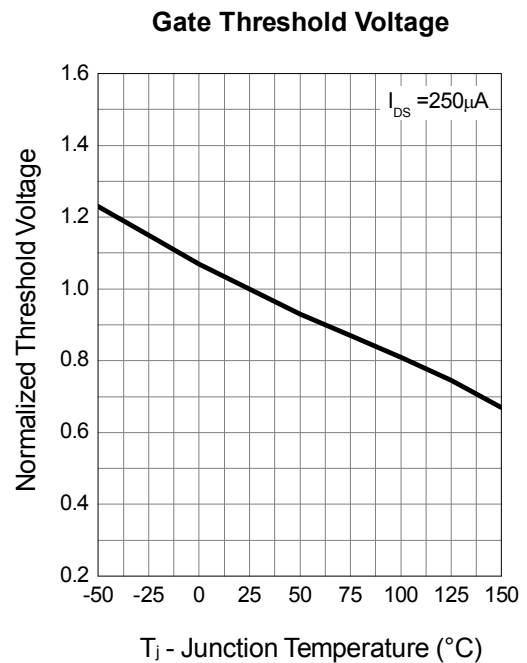
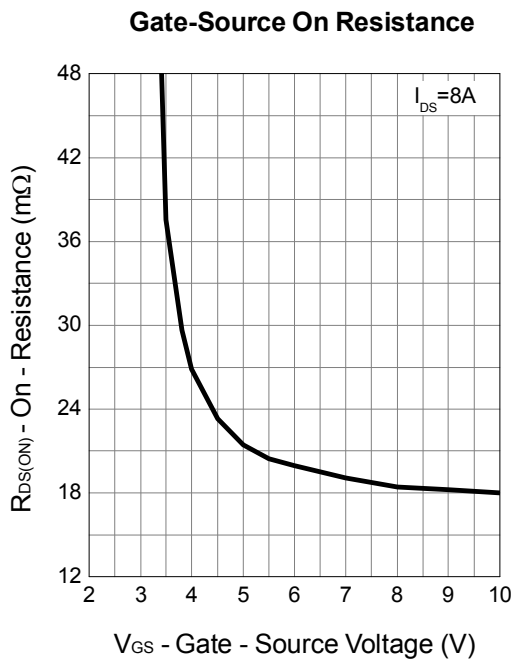
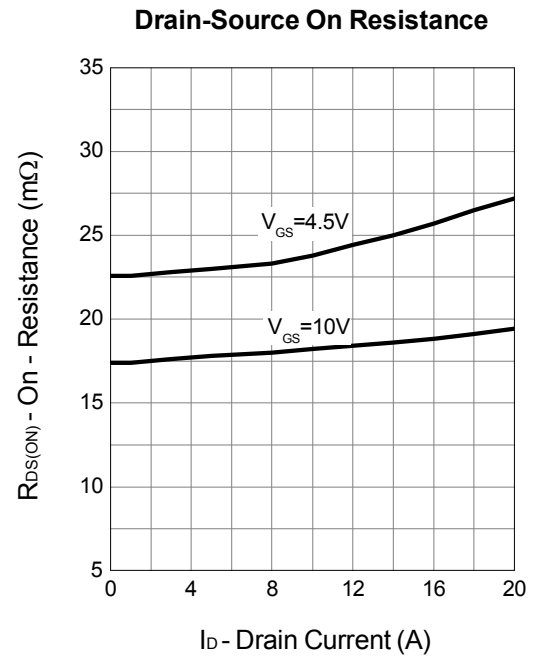
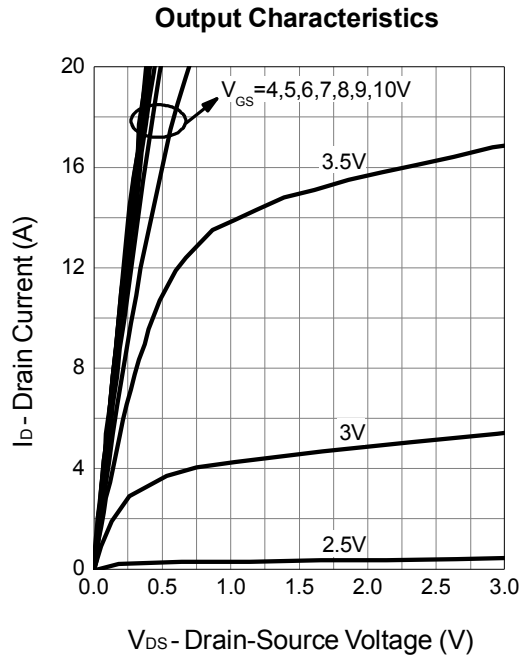
Typical Characteristics

Channel 1



Typical Characteristics (Cont.)

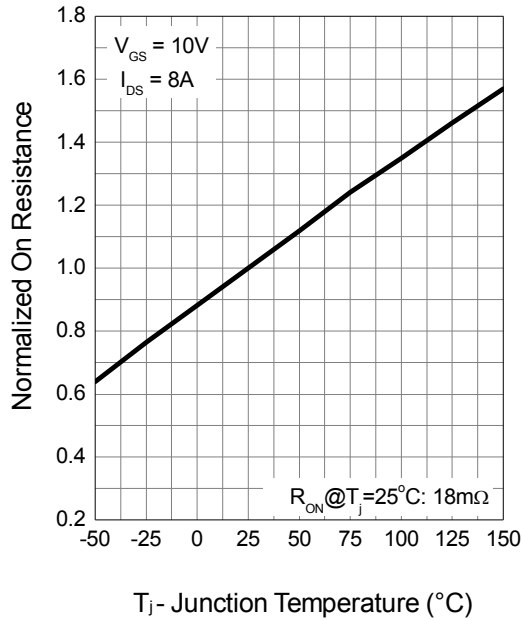
Channel 1



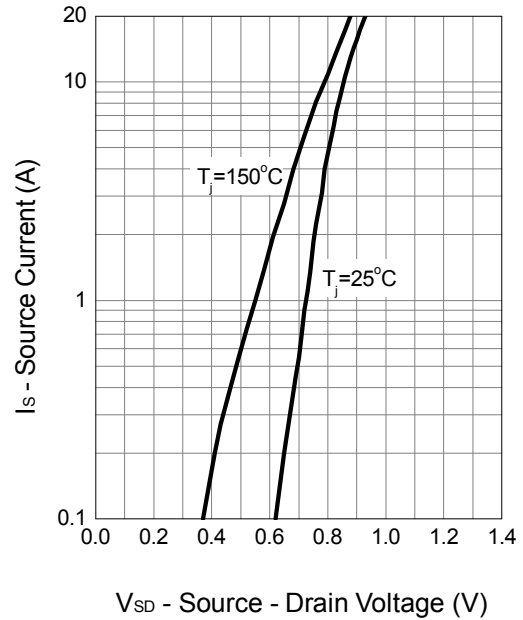
Typical Characteristics (Cont.)

Channel 1

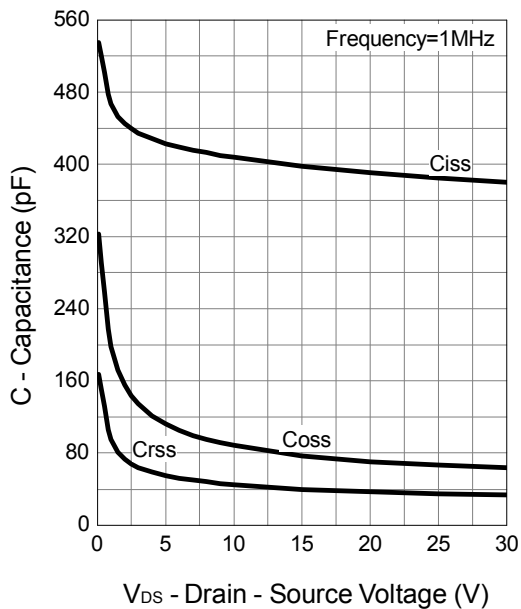
Drain-Source On Resistance



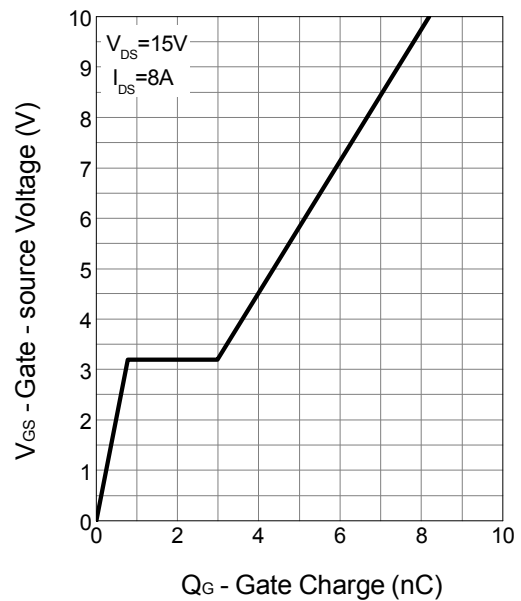
Source-Drain Diode Forward



Capacitance

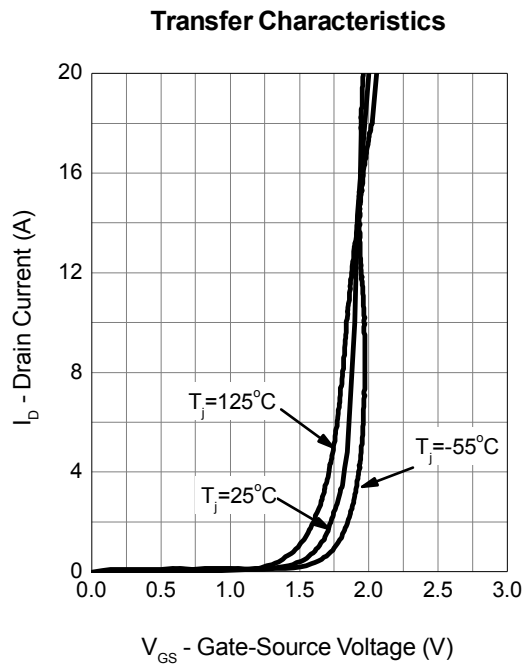


Gate Charge



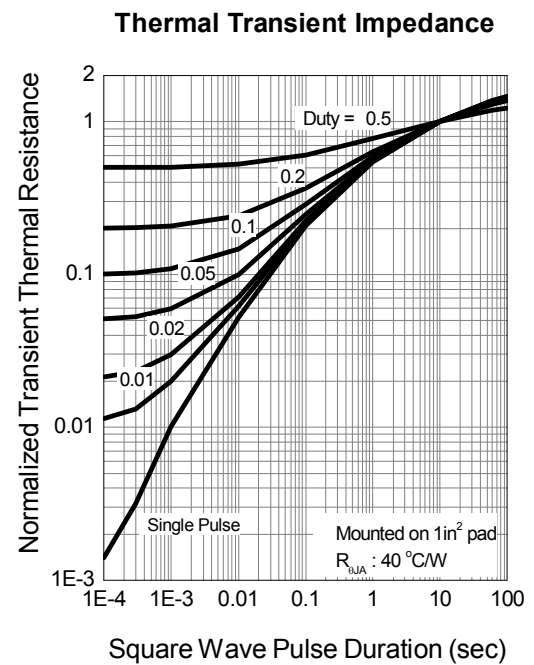
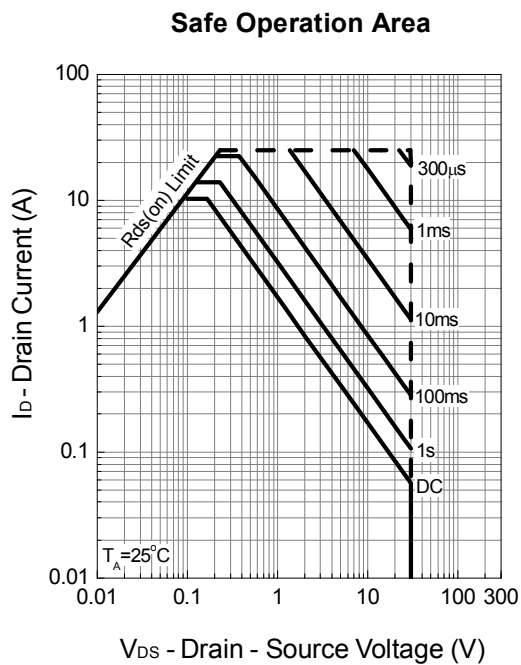
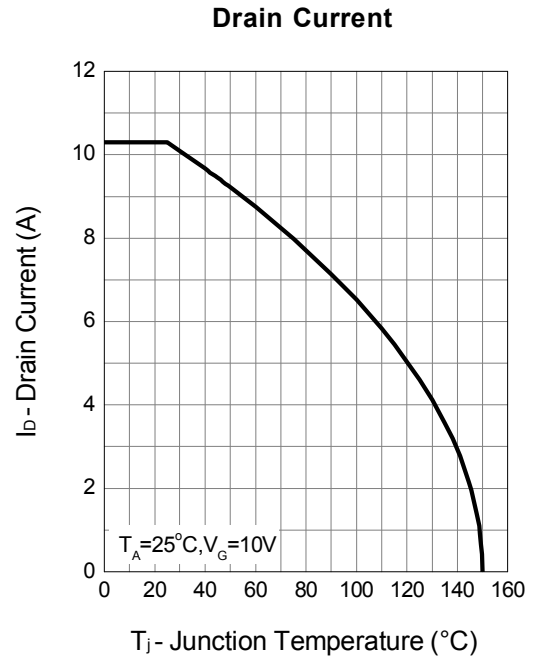
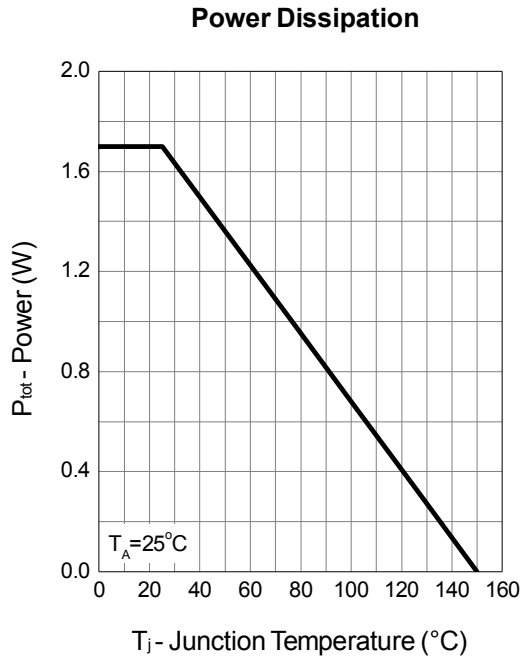
Typical Characteristics (Cont.)

Channel 1



Typical Characteristics (Cont.)

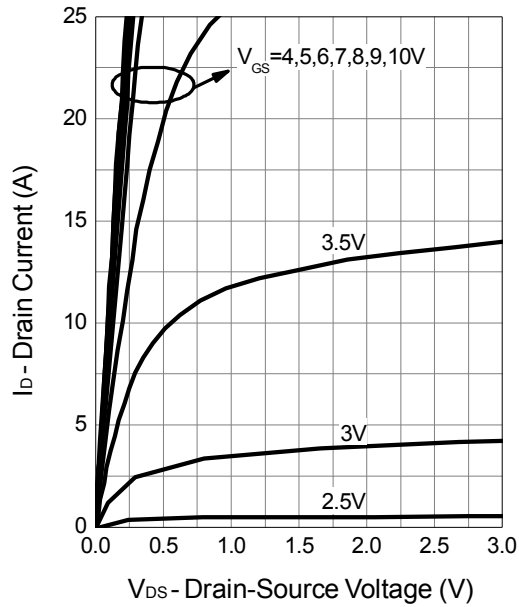
Channel 2



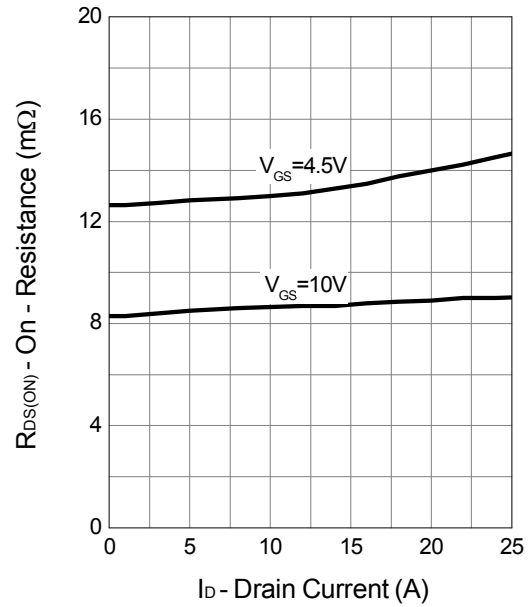
Typical Characteristics (Cont.)

Channel 2

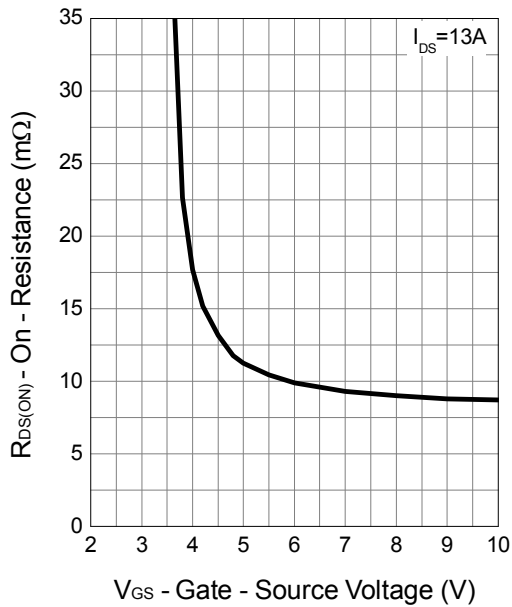
Output Characteristics



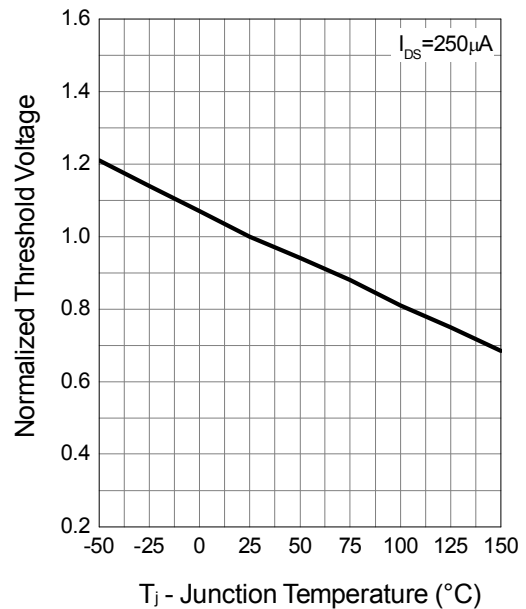
Drain-Source On Resistance



Gate-Source On Resistance



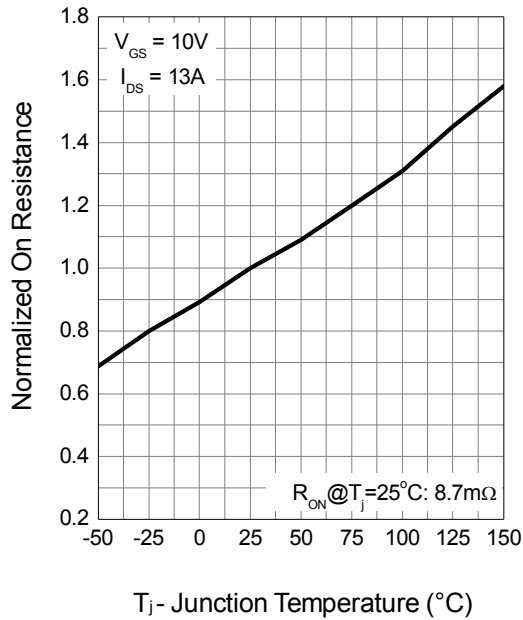
Gate Threshold Voltage



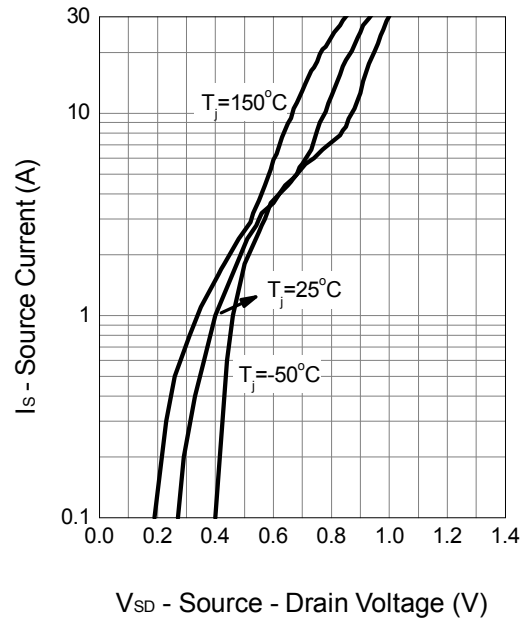
Typical Characteristics (Cont.)

Channel 2

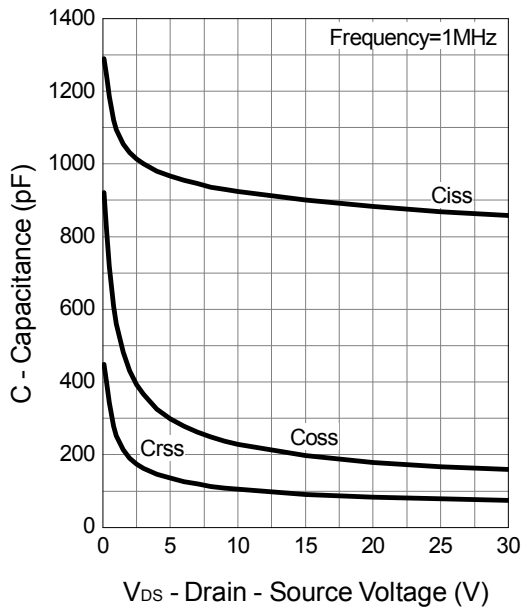
Drain-Source On Resistance



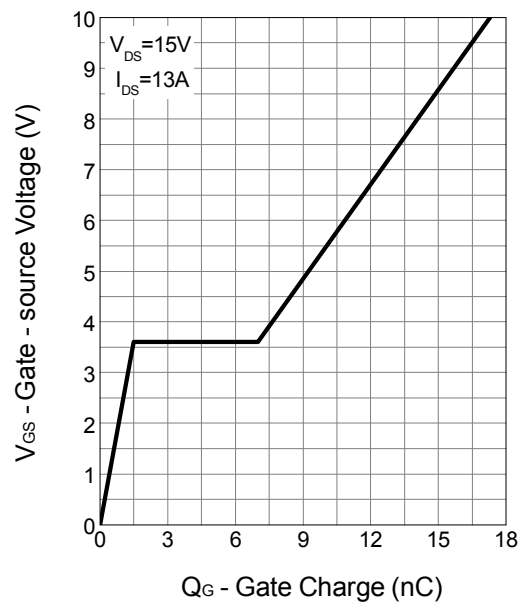
Source-Drain Diode Forward



Capacitance

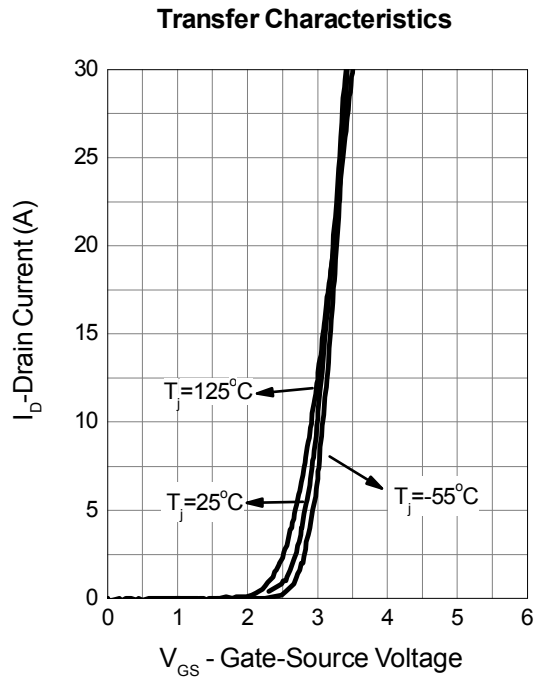


Gate Charge



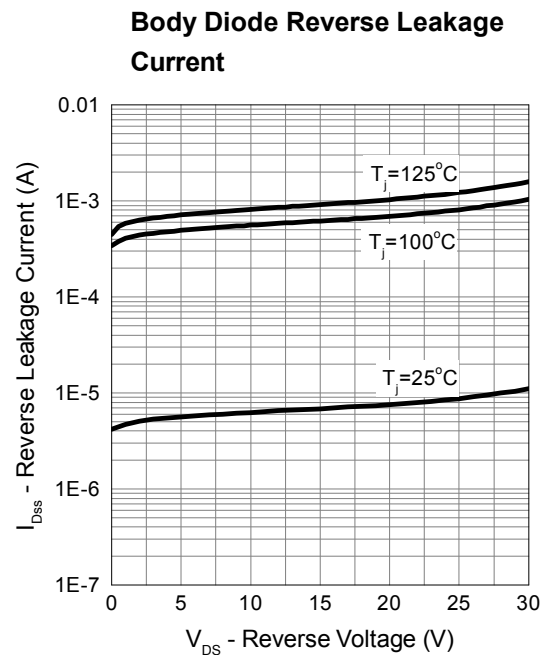
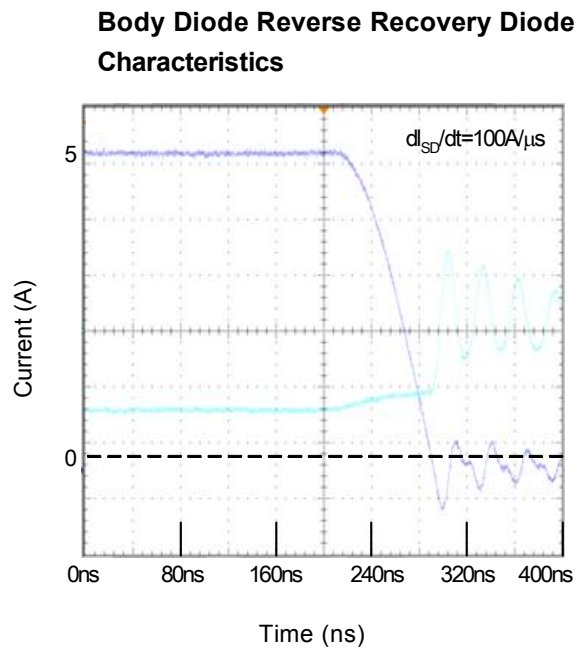
Typical Characteristics (Cont.)

Channel 2

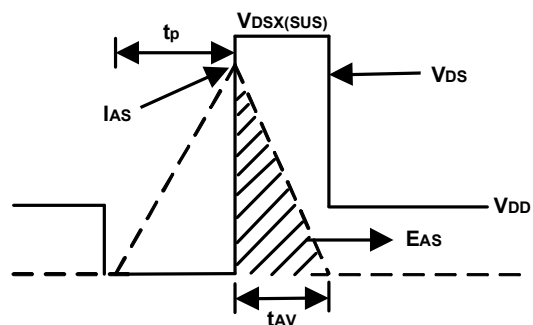
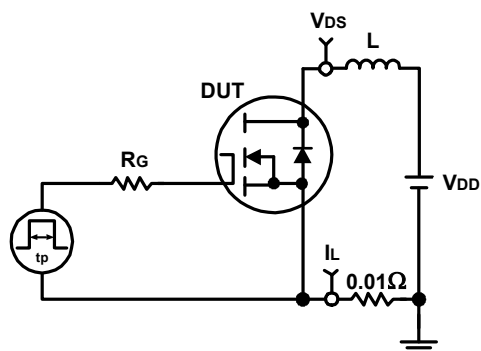


Schottky Body Diode Characteristics

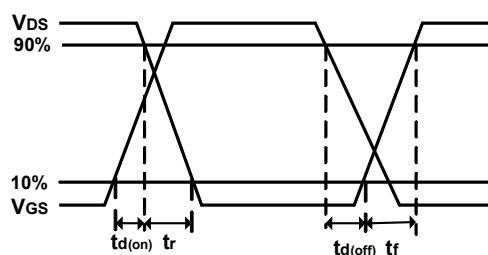
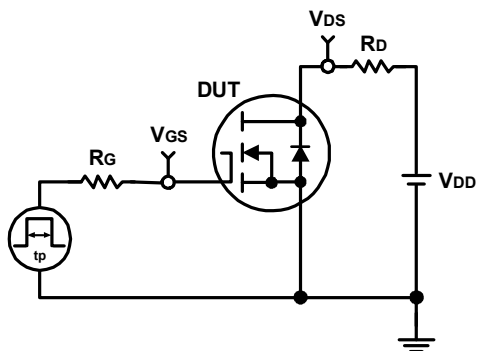
Channel 2



Avalanche Test Circuit and Waveforms

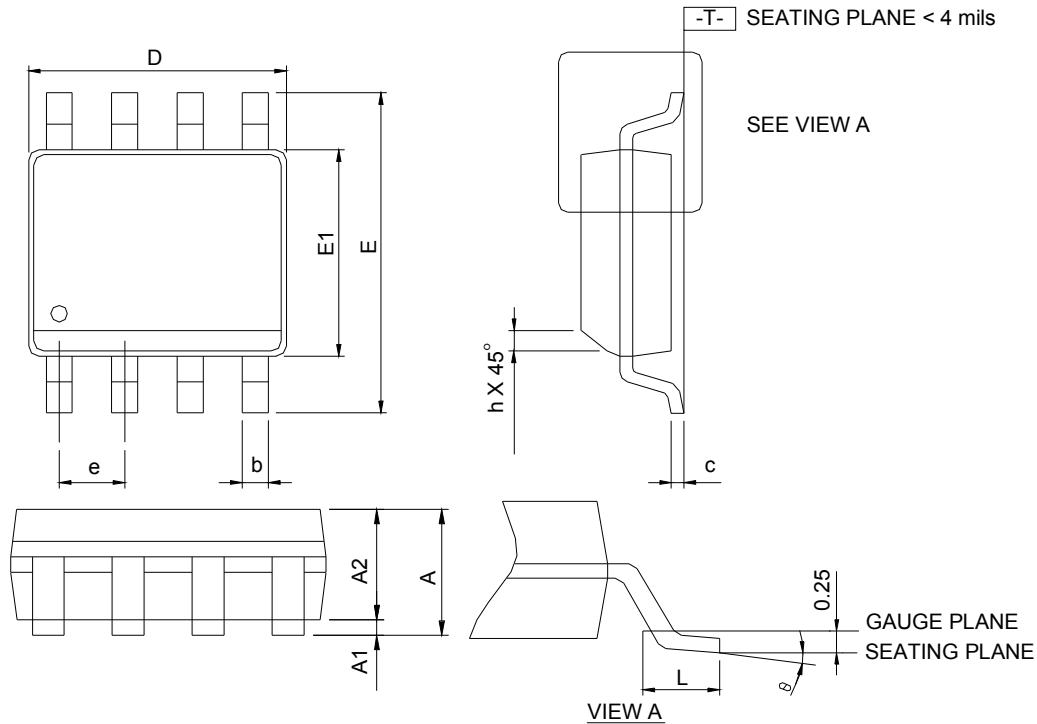


Switching Time Test Circuit and Waveforms



Package Information

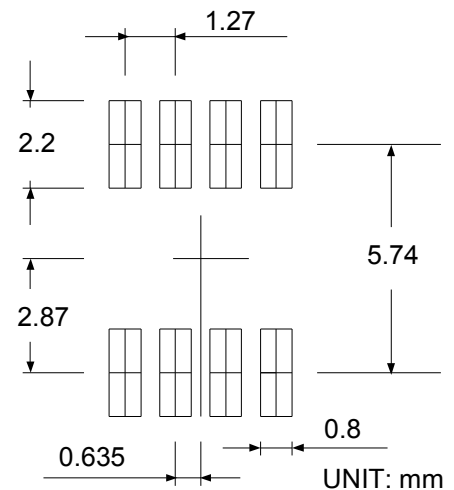
SOP-8



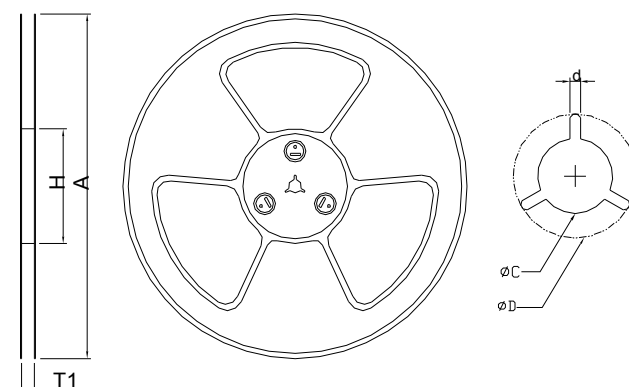
DIMENSIONS	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.75	-	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

- Note: 1. Follow JEDEC MS-012 AA.
 2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
 3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.

RECOMMENDED LAND PATTERN



Technical drawing of a multi-hole plate. The main view shows a rectangular plate with three rows of holes. The top row has six circular holes with diameter $\varnothing D0$. The middle row has three rectangular holes with diameter $\varnothing D1$. The bottom row has three rectangular holes with diameter $\varnothing D1$. Dimensions include $P0$, $P2$, $P1$ for horizontal spacing; $B0$, $A0$, B for vertical spacing; $E1$, F , W for overall dimensions; and $K0$ for a side feature. Two cross-sections are shown: SECTION A-A (top) and SECTION B-B (bottom). SECTION A-A shows a profile with a central hole and a side feature. SECTION B-B shows a profile with a central hole and a side feature.

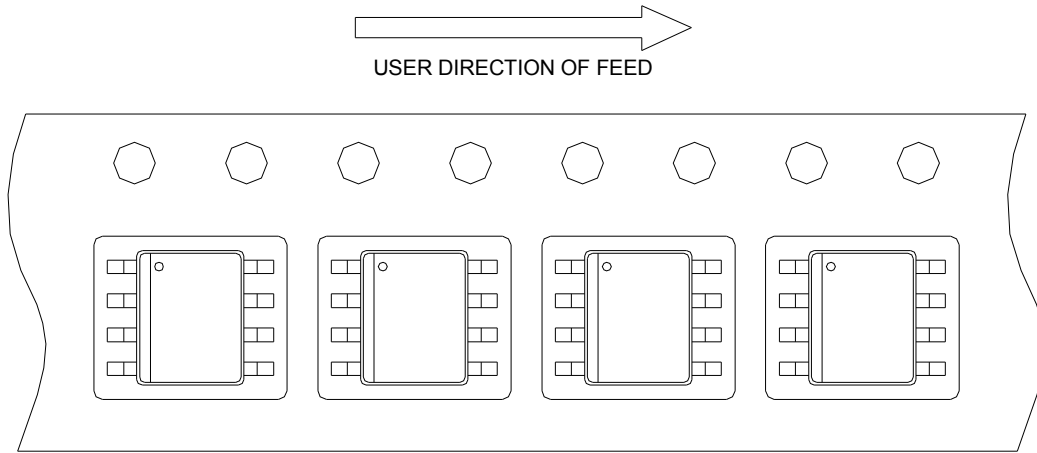


Application	A	H	T1	C	d	D	W	E1	F
SOP-8	330.0± 2.00	50 MIN.	12.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	12.0±0.30	1.75±0.10	5.5±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	8.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.5 MIN.	0.6+0.00 -0.40	6.40±0.20	5.20±0.20	2.10±0.20

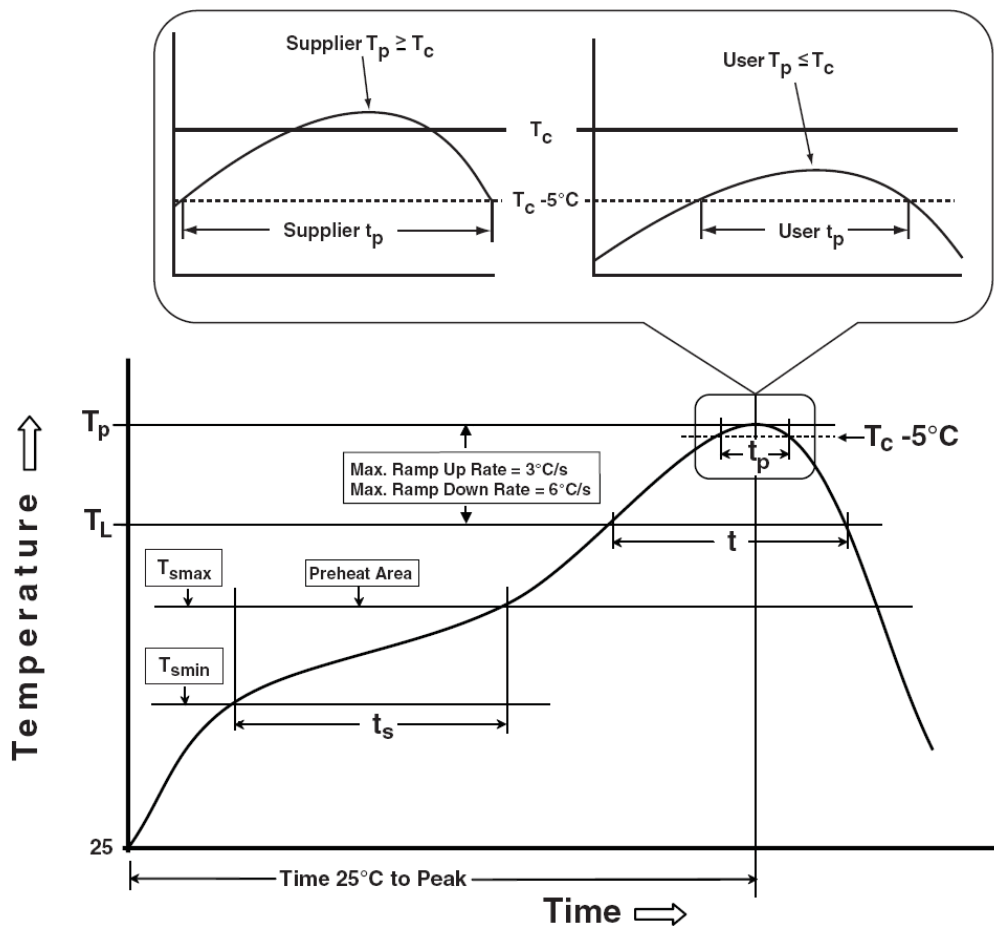
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Taping Direction Information

SOP-8



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak Temperature min (T_{smin}) Temperature max (T_{smax}) Time (T_{smin} to T_{smax}) (t_s)	100 °C 150 °C 60-120 seconds	150 °C 200 °C 60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L) Time at liquidous (t_L)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum. ** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

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